

Excellent Integrated System Limited

Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-20ETS08FPPBF</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-20ETS08FPPBF - DIODE GEN PURP 800V 20A TO220FP





VS-20ETS..FPPbF Series, VS-20ETS..FP-M3 Series

www.vishay.com

Vishay Semiconductors

HALOGEN

FREE

High Voltage, Input Rectifier Diode, 20 A





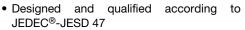
				1
TO-220	FIII	1	_P	ΔK

2	
1	3
Cathode	Anode

PRODUCT SUMMARY		
Package	TO-220FP	
I _{F(AV)}	20 A	
V _R	800 V to 1200 V	
V _F at I _F	1.1 V	
I _{FSM}	300 A	
T _J max.	150 °C	
Diode variation	Single die	

FEATURES

- · Very low forward voltage drop
- 150 °C max. operating junction temperature
- · Glass passivated pellet chip junction



- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 approved
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Input rectification
- · Vishay Semiconductors switches and output rectifiers which are available in identical package outlines

DESCRIPTION

High voltage rectifiers optimized for very low forward voltage drop with moderate leakage.

These devices are intended for use in main rectification (single or three phase bridge).

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter T _A = 55 °C, T _J = 125 °C common heatsink of 1 °C/W	18	22	А		

MAJOR RATINGS AND CHARACTERISTICS				
SYMBOL	CHARACTERISTICS	VALUES	UNITS	
I _{F(AV)}	Sinusoidal waveform	20	А	
V_{RRM}	Range	800/1200	V	
I _{FSM}		300	A	
V _F	10 A, T _J = 25 °C	1.0	V	
TJ		-40 to +150	°C	

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} AT 150 °C mA		
VS-20ETS08FPPbF, VS-20ETS08FP-M3	800	900	1		
VS-20ETS12FPPbF, VS-20ETS12FP-M3	1200	1300	1		

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ABSOLUTE MAXIMUM RATING	S			
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current	I _{F(AV)}	T _C = 51 °C, 180° conduction half sine wave	20	
Maximum peak one cycle		10 ms sine pulse, rated V _{RRM} applied	250	Α
non-repetitive surge current	I _{FSM}	10 ms sine pulse, no voltage reapplied	300	
Maximum 12t for funing	l ² t	10 ms sine pulse, rated V _{RRM} applied	316	A ² s
Maximum I ² t for fusing	1-1	10 ms sine pulse, no voltage reapplied	442	A-S
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied	4420	A²√s

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS VALUES UNI			UNITS
Maximum forward voltage drop	V _{FM}	20 A, T _J = 25 °C		1.1	V
Forward slope resistance	r _t	$T_{\rm J} = 150 ^{\circ}{\rm C}$ $\frac{10.4}{0.85}$		10.4	mΩ
Threshold voltage	V _{F(TO)}			0.85	V
Maximum rayaraa laakaga aurrant		T _J = 25 °C		0.1	mA
Maximum reverse leakage current	IRM	T _J = 150 °C	V _R = Rated V _{RRM}	1.0	IIIA

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +150	°C	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	2.8		
Maximum thermal resistance, junction to ambient	R _{thJA}		62	°C/W	
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, and greased	0.5		
Approximate weight			2	g	
Approximate weight			0.07	OZ.	
Mounting torque minimum			6.0 (5.0)	kgf · cm	
Mounting torque maximum	m		12 (10)	(lbf · in)	
Modine davice		Coop at the TO 200 FULL DAY	20ETS08FP		
Marking device		Case style TO-220 FULL-PAK	20ETS	S12FP	

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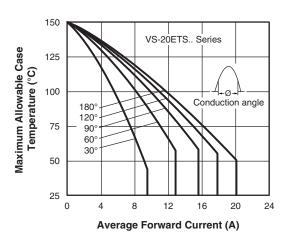


Fig. 1 - Current Rating Characteristics

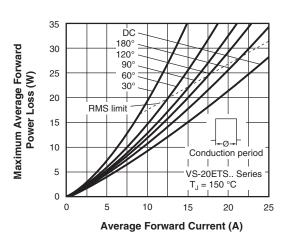


Fig. 4 - Forward Power Loss Characteristics

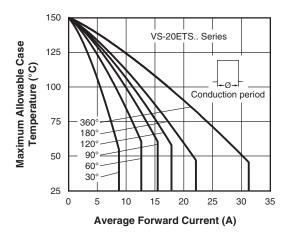


Fig. 2 - Current Rating Characteristics

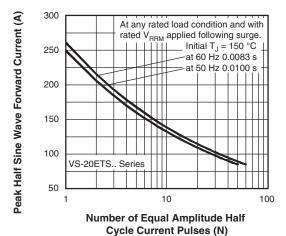


Fig. 5 - Maximum Non-Repetitive Surge Current

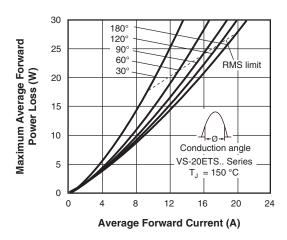


Fig. 3 - Forward Power Loss Characteristics

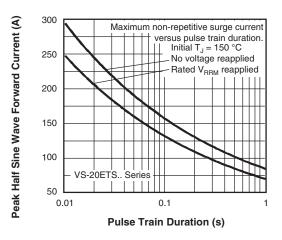


Fig. 6 - Maximum Non-Repetitive Surge Current

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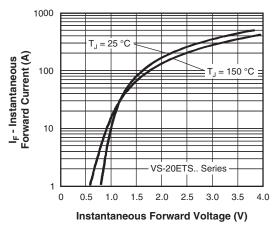


Fig. 7 - Forward Voltage Drop Characteristics

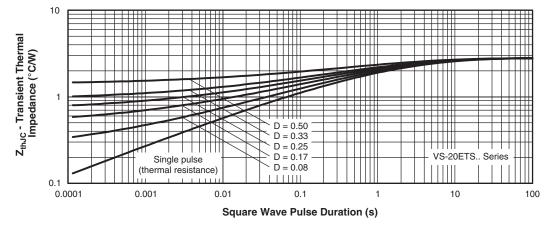


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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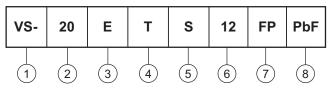
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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

Current rating (20 = 20 A)

Circuit configuration:

3 E = single diode

Package:

4 T = TO-220

Type of silicon:

S = standard recovery rectifier

08 = 800 V 6 Voltage ratings 12 = 1200 V

FULL-PAK

Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-20ETS08FPPbF	50	1000	Antistatic plastic tubes	
VS-20ETS08FP-M3	50	1000	Antistatic plastic tubes	
VS-20ETS12FPPbF	50	1000	Antistatic plastic tubes	
VS-20ETS12FP-M3	50	1000	Antistatic plastic tubes	

LINKS TO RELATED DOCUMENTS			
Dimensions		www.vishay.com/doc?95005	
Dort marking information	TO-220 FP PbF	www.vishay.com/doc?95009	
Part marking information	TO-220 FP -M3	www.vishay.com/doc?95440	

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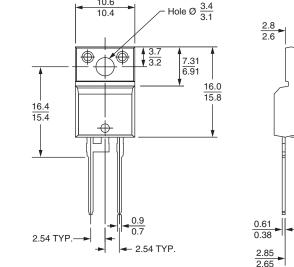
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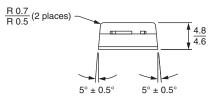


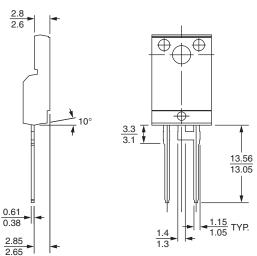
Outline Dimensions

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DIMENSIONS in millimeters







Lead assignments **Diodes** 1 + 2 - Cathode

3 - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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